# XN0NE92

## Silicon P-channel MOSFET (FET) Silicon epitaxial planar type (SBD)

### For DC-DC converter

### ■ Features

- Two elements incorporated into one package
- Reduction of the mounting area and assembly cost by one half
- High-speed switching, low on resistance

## ■ Absolute Maximum Ratings $T_a = 25$ °C

					2. Cata	
	Parameter	Symbol	Rating	Unit	3: Gate	
FET	Drain-source surrender	V <sub>DSS</sub>	-12	V	■ Markin	na s
	voltage				- Warkin	9
	Gate-source surrender	V <sub>GSS</sub>	±15	V		
	voltage				Interna	al C
	Drain current	$I_D$	-1.2	A		
	Peak drain current	$I_{DP}$	-3	A		
	Total power dissipation *	$P_{T}$	600	mW		
	Channel temperature	$T_{ch}$	125	°C		χ¢
	Storage temperature	T <sub>stg</sub>	-55 to +125	°C	L about la	7
SBD	Reverse voltage	$V_R$	20	V	all	c
	Repetitive peak reverse voltage	$V_{RRM}$	25	V	300 :(0	Ò.
	Forward current (Average)	I <sub>F(AV)</sub>	700	mA	r'o alli	
	Non-repetitive peak	I <sub>FSM</sub>	2	A	150	
	forward surge current				.101	
Note) *:	Measuring on ceramic substrate	e at 15 mm	$1 \times 15 \text{ mm} \times 0$	.6 mm	0.,,	
	$A \rightarrow C$			NC.	,	
■ Elec	trical Characteristics T	$C_a = 25^{\circ}C$	$C \pm 3^{\circ}C$	OUL		
• FET			·x RO			
	Parameter	Symbo	A ALI	Condition	ıs	Mi
Drain-s	ource surrender voltage	Voss	√2 1 m/	$A, V_{GS} = 0$		-1
Drain-s	ource cutoff current	I <sub>DSS</sub> ×	$V_{DS} = -10$	$V, V_{GS} = 0$		
Gate-so	ource cutoff current	$I_{GSS}$	$V_{GS} = \pm 8$	$V, V_{DS} = 0$		
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Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Drain-source surrender voltage	VDSS	$V_{GS} = 0$	-12			V	
Drain-source cutoff current	$I_{\mathrm{DSS}}$	$\dot{V}_{DS} = -10 \text{ V},  V_{GS} = 0$			-1	V	
Gate-source cutoff current	$I_{GSS}$	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0$			±10	V	
Gate threshold voltage	V <sub>th</sub>	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$	- 0.4		-1.3	V	
Forward transfer admittance *	Yfs	$V_{DS} = -10 \text{ V}, I_{D} = -800 \text{ mA}$	0.8	1.1		S	
Drain-source ON resistance *	R <sub>DS(on)</sub>	$V_{GS} = -4 \text{ V}, I_D = -800 \text{ mA}$		350	450	mΩ	
Turn-on time	t <sub>on</sub>	$V_{DD} = -10 \text{ V}, R_L = 12.5 \Omega,$		15		ns	
Storage time	t <sub>stg</sub>	$I_D = -800 \text{ mA}, V_{GS} = 0 \text{ V to } -4 \text{ V}$		10		ns	
Turn-off time	t <sub>off</sub>			10		ns	

- Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
  - 2. Observe precautions for handling. Electrostatic sensitive devices.
  - 3. \*: Pulse measurement

## Package

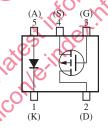
 Code Mini5-G1 (Exclusive use for XN0NE92)

Pin Name

1: Cathode 4: Source 2: Drain 5: Anode 3: Gate

■ Marking Symbol: 3F

■ Internal Connection



Publication date: April 2008 SJJ00308BED

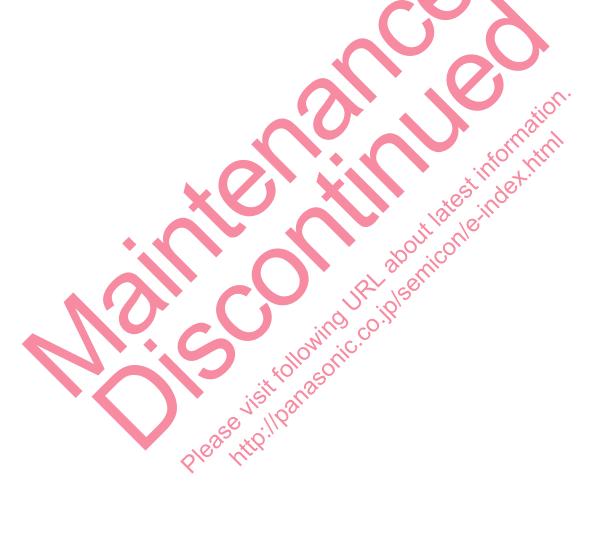
## ■ Electrical Characteristics (continued) $T_a = 25$ °C $\pm 3$ °C

## • SBD

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Forward voltage	V <sub>F</sub>	$I_F = 700 \text{ mA}$			0.45	V
Reverse current	$I_R$	$V_R = 20 \text{ V}$			200	μΑ
Terminal capacitance	$C_{t}$	$V_R = 0$ , $f = 1$ MHz		100		pF
Reverse recovery time	t <sub>rr</sub>	$I_F = I_R = 100 \text{ mA}$		7		ns
		$I_{rr} = 10 \text{ mA}, R_L = 100 \Omega$				

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for diodes.

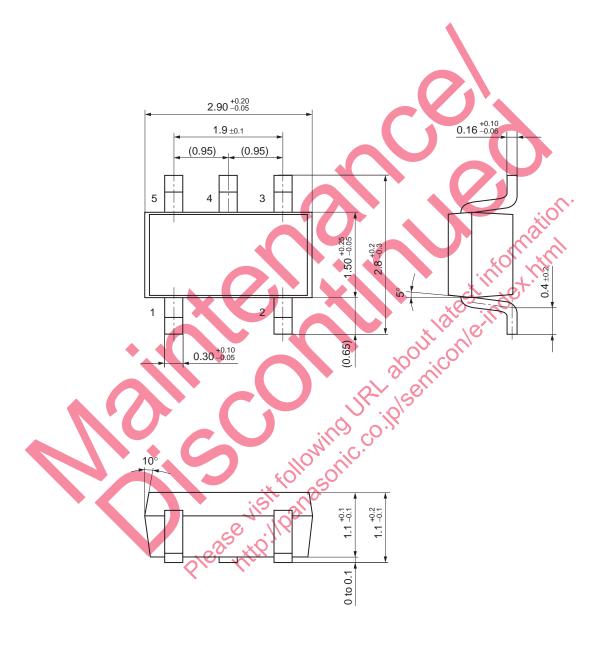
2. Schottky barrier diode is frail with static electricity, and it should be kept in safety from shock of static electricity and static electricity level.



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Mini5-G1 (Exclusive use for XN0NE92)





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